

New Product

P-Channel 20-V (D-S) MOSFET

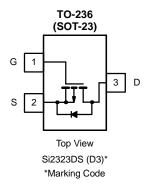
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(\Omega)$	I _D (A)		
	0.039 @ V _{GS} = -4.5 V	-4.7		
-20	0.052 @ V _{GS} = -2.5 V	- 4.1		
	0.068 @ V _{GS} = -1.8 V	- 3.5		

FEATURES

• TrenchFET® Power MOSFET

APPLICATIONS

- Load Switch
- PA Switch



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 sec	Steady State	Unit
Drain-Source Voltage		V _{DS}	-20		V
Gate-Source Voltage		V _{GS}	±8		
Continuous Drain Current (T ₁ = 150°C) ^{a, b}	T _A = 25°C		- 4.7	-3.7	
Continuous Diain Current (1) = 150 C) 4.5	T _A = 70°C	ID	-3.8	-2.9	А
Pulsed Drain Current		I _{DM}	-20		^
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	-1.0	-0.6	
Manifestore Description 2 h	T _A = 25°C	D	1.25	0.75	10/
Maximum Power Dissipation ^{a, b}	T _A = 70°C	P_{D}	0.8	0.48	W
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 5 sec	R _{thJA}	75	100		
Maximum Junction-to-Ambient ^a	Steady State		120	166	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.
b. Pulse width limited by maximum junction temperature.

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Parameter	Symbol	Test Conditions	Limits				
			Min	Тур	Max	Unit	
Static			•	•		•	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.40		-1.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		V_{DS} = -16 V, V_{GS} = 0 V			-1	μΑ	
	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-20			А	
		$V_{GS} = -4.5 \text{ V}, I_D = -4.7 \text{ A}$		0.031	0.039	Ω	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5$ V, $I_{D} = -4.1$ A		0.041	0.052		
		$V_{GS} = -1.8$ V, $I_{D} = -2.0$ A		0.054	0.068		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -5 \text{ V}, I_{D} = -4.7 \text{ A}$		16		S	
Diode Forward Voltage	V _{SD}	I _S = -1.0 A, V _{GS} = 0 V		0.7	-1.2	V	
Dynamic ^b							
Total Gate Charge	Q_{g}			12.5	19	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_{D} \cong -4.7 \text{ A}$		1.7			
Gate-Drain Charge	Q _{gd}			3.3			
Input Capacitance	C _{iss}			1020		pF	
Output Capacitance	C _{oss}	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz		191			
Reverse Transfer Capacitance	C _{rss}			140			
Switching ^c				•			
Turn-On Time	t _{d(on)}			25	40		
	t _r	$V_{DD} = -10 \text{ V, R}_{L} = 10 \Omega$ $I_{D} \cong -1.0 \text{ A, V}_{GEN} = -4.5 \text{ V}$		43	65	ns	
Turn-Off Time	t _{d(off)}	$R_{G} = 6 \Omega$		71	110	113	
Turn-Off Time	t _f			48	75	1	

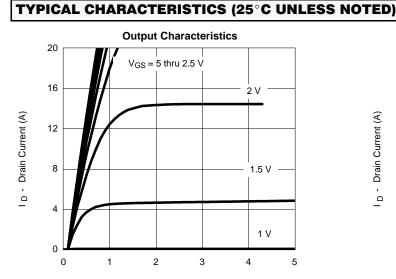
Notes

- a. Pulse test: PW ≤ 300 µs duty cycle ≤ 2%.
 b. For DESIGN AID ONLY, not subject to production testing.
 c. Switching time is essentially independent of operating temperature.

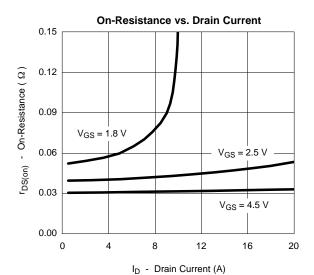


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V_{DS} - Drain-to-Source Voltage (V)

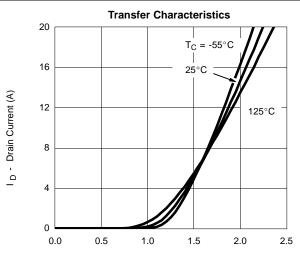


Gate Charge

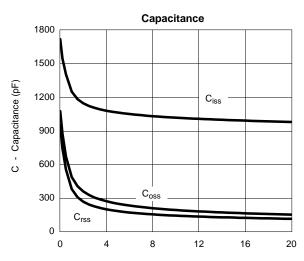
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V_{DS} = 6 V
I_D = 4.7 A

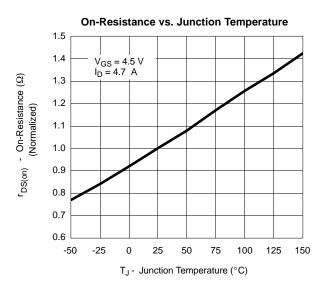
Q_g - Total Gate Charge (nC)



V_{GS} - Gate-to-Source Voltage (V)



V_{DS} - Drain-to-Source Voltage (V)

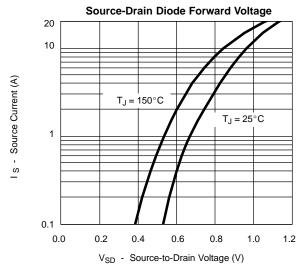


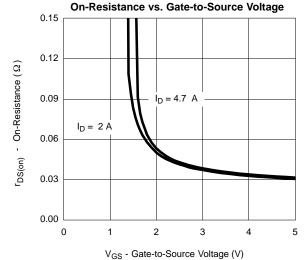
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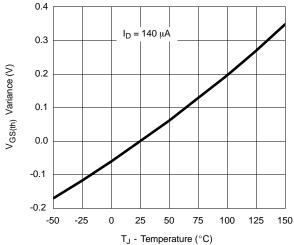


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

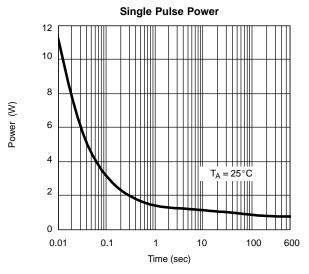




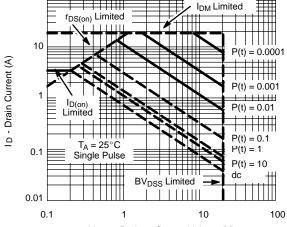








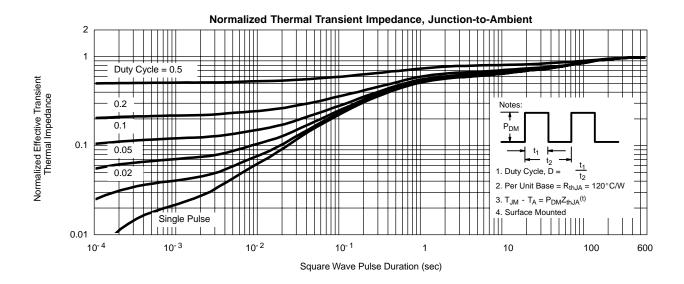




V_{DS} - Drain-to-Source Voltage (V)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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Legal Disclaimer Notice



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